

8961726 TEXAS INSTR (OPT0)

62C 36976 D

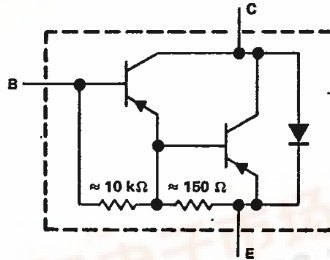
TIP645, TIP646, TIP647
P-N-P DARLINGTON-CONNECTED
SILICON POWER TRANSISTORS

REVISED OCTOBER 1984

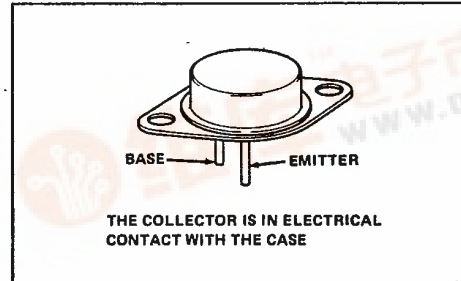
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- Designed For Complementary Use With TIP640, TIP641, TIP642
- 175 W at 25°C Case Temperature
- 10 A Rated Collector Current
- Min h_{FE} of 1000 at 4 V, 5 A
- 100 mJ Reverse Energy Rating

device schematic



TO-3 PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIP645	TIP646	TIP647
Collector-base voltage	-60 V	-80 V	-100 V
Collector-emitter voltage ($I_B = 0$)	-60 V	-80 V	-100 V
Emitter-base voltage		-5 V	
Continuous collector current		-10 A	
Peak collector current (see Note 1)		-15 A	
Continuous base current		-0.5 A	
Safe operating areas at (or below) 25°C case temperature	See Figures 7 and 8		
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	175 W		
Continuous device dissipation at (or below) 25°C free-air temperature (see Note 3)	5 W		
Unclamped inductive load energy (see Note 4)	100 mJ		
Operating collector junction and storage temperature range	-65°C to 200°C		
Lead temperature 3,2 mm (0.125 inch) from case for 10 seconds	260°C		

- NOTES:
1. This value applies for $t_W < 0.3$ ms, duty cycle $< 10\%$.
 2. Derate linearly to 200°C case temperature at the rate of 1 W/°C or refer to Dissipation Derating Curve, Figure 9.
 3. Derate linearly to 200°C free-air temperature at the rate of 28.6 mW/°C or refer to Dissipation Derating Curve, Figure 10.
 4. This rating is based on the capability of the transistors to operate safely in the circuit of Figure 2. $L = 20$ mH, $R_{BB2} = 100 \Omega$, $V_{BB2} = 0$ V, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V, Energy $\approx I_C^2 L / 2$.



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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	TIP645			TIP646			TIP647			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CEO}$	$I_C = -30 \text{ mA}$, See Note 5 $I_B = 0$	-60			-80			-100			V
I_{CEO}	$V_{CE} = -30 \text{ V}$, $I_B = 0$			-2							mA
	$V_{CE} = -40 \text{ V}$, $I_B = 0$						-2				
	$V_{CE} = -50 \text{ V}$, $I_B = 0$								-2		
I_{CBO}	$V_{CB} = -60 \text{ V}$, $I_E = 0$			-1							mA
	$V_{CB} = -80 \text{ V}$, $I_E = 0$						-1				
I_{EBO}	$V_{CB} = -100 \text{ V}$, $I_E = 0$								-1		mA
	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-2			-2		-2		
h_{FE}	$V_{CE} = -4 \text{ V}$, See Notes 5 and 6 $I_C = -5 \text{ A}$	1000			1000			1000			
	$V_{CE} = -4 \text{ V}$, See Notes 5 and 6 $I_C = -10 \text{ A}$	600			500			600			
V_{BE}	$V_{CE} = -4 \text{ V}$, See Notes 5 and 6 $I_C = -10 \text{ A}$			-3			-3		-3		V
$V_{CE(sat)}$	$I_B = -10 \text{ mA}$, See Notes 5 and 6 $I_C = -5 \text{ A}$			-2			-2		-2		V
	$I_B = -40 \text{ mA}$, See Notes 5 and 6 $I_C = -10 \text{ A}$			-3			-3		-3		
V_F	$I_F = 10 \text{ A}$, See Notes 5 and 6			3.5			3.5		3.5		V

NOTES: 5. These parameters must be measured using pulse techniques, $t_w = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3,2 mm (0.125 inch) from the device body.

resistive-load switching characteristic at 25°C case temperature

PARAMETER	TEST CONDITIONS†	MIN	TYP	MAX	UNIT
t_{on}	$I_C = -10 \text{ A}$, $I_{B1} = -40 \text{ mA}$, $I_{B2} = 40 \text{ mA}$		0.9		μs
t_{off}	$V_{BE(off)} = 4.2 \text{ V}$, $R_L = 3 \Omega$, See Figure 1		11		

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

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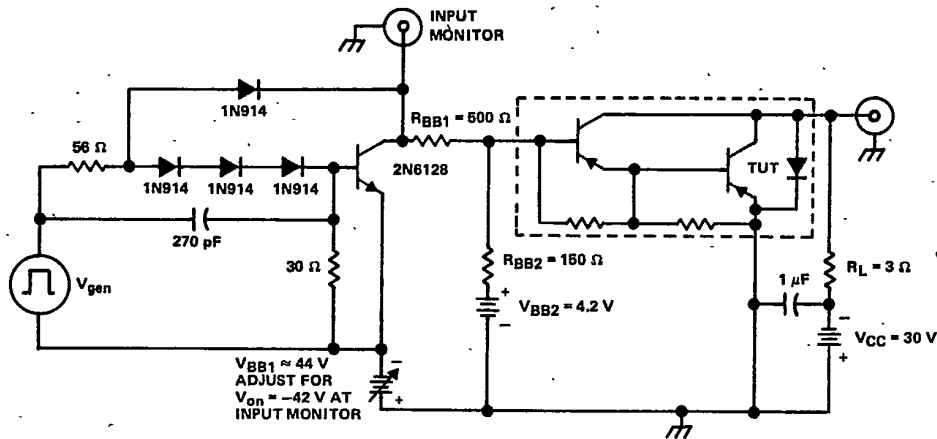
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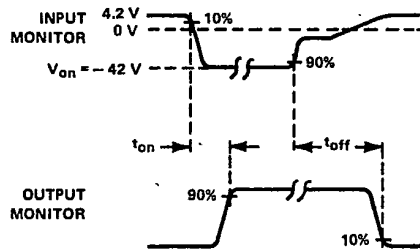
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PARAMETER MEASUREMENT INFORMATION

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TEST CIRCUIT



VOLTAGE WAVEFORMS

- NOTES:
- A. V_{gen} is a 30-V pulse into a 50 Ω termination.
 - B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r < 15$ ns, $t_f < 15$ ns, $Z_{out} = 50$ Ω , $t_w = 20$ μ s, duty cycle ≤ 2 %.
 - C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15$ ns, $R_{in} > 10$ M Ω , $C_{in} < 11.5$ pF.
 - D. Resistors must be noninductive types.
 - E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING



TIP Devices

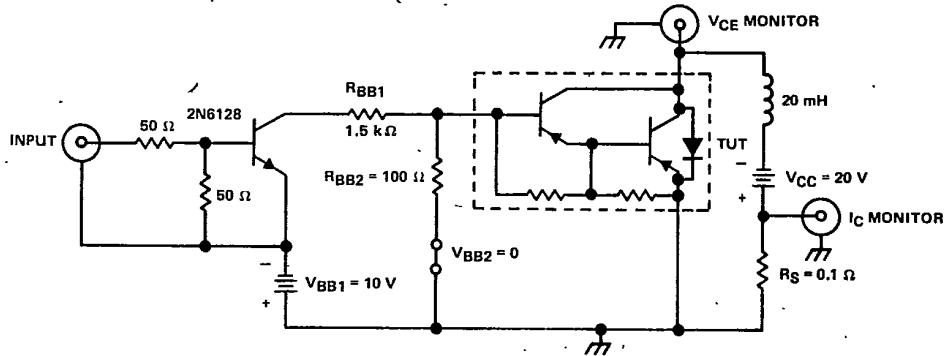
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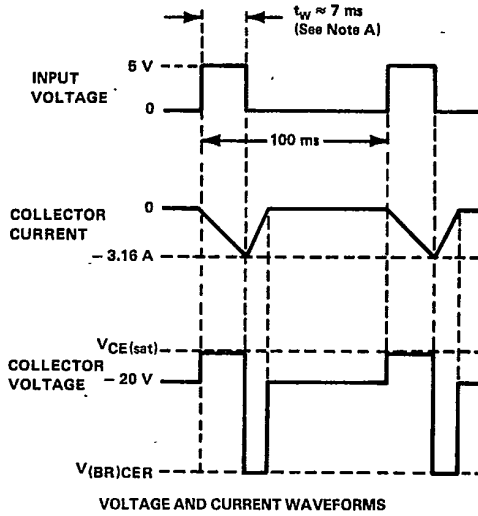
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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

NOTE A: Input pulse duration is increased until $I_{CM} = -3.16 \text{ A}$.

FIGURE 2. INDUCTIVE-LOAD SWITCHING

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TYPICAL CHARACTERISTICS

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STATIC FORWARD CURRENT TRANSFER RATIO
 VS
 COLLECTOR CURRENT

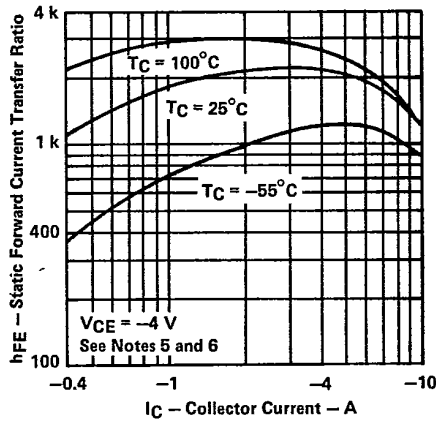


FIGURE 3

BASE-EMITTER VOLTAGE
 VS
 CASE TEMPERATURE

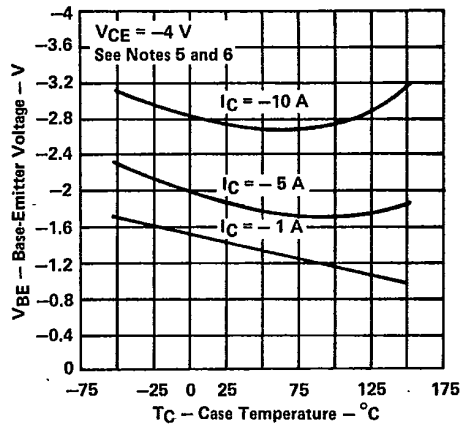


FIGURE 4

COLLECTOR-EMITTER SATURATION VOLTAGE
 VS
 CASE TEMPERATURE

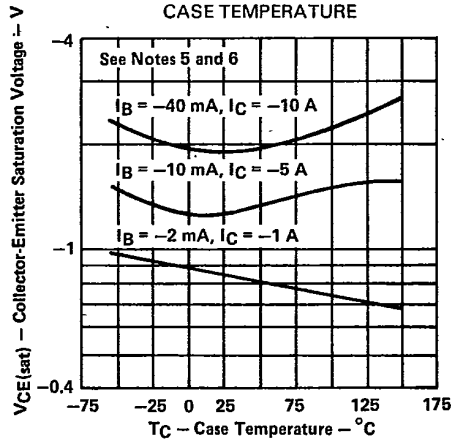


FIGURE 5

SMALL-SIGNAL COMMON-EMITTER
 FORWARD CURRENT TRANSFER RATIO
 VS
 FREQUENCY

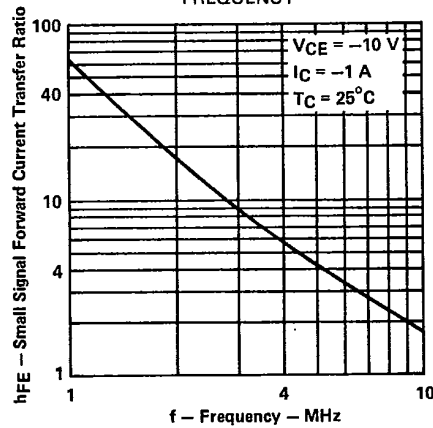


FIGURE 6

- NOTES: 5. These parameters must be measured using pulse techniques, $t_w = 300 \mu s$, duty cycle $\leq 2\%$.
 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3,2 mm (0.125 inch) from the device body.



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MAXIMUM SAFE OPERATING AREA

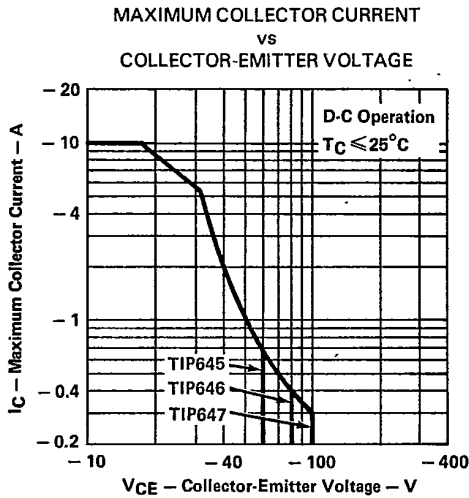


FIGURE 7

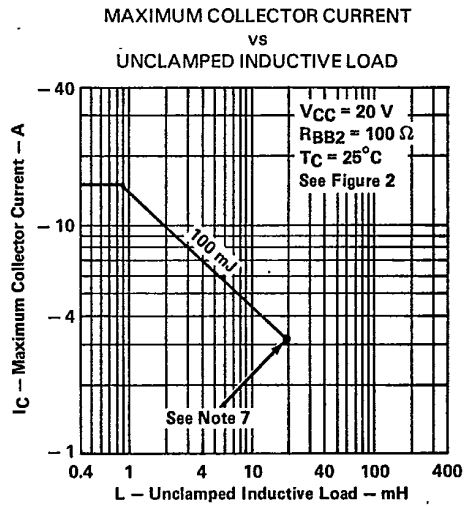


FIGURE 8

NOTE 7: Above this point the safe operating area has not been defined.

THERMAL INFORMATION

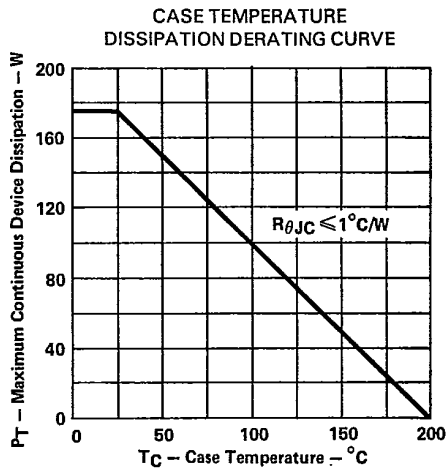


FIGURE 9

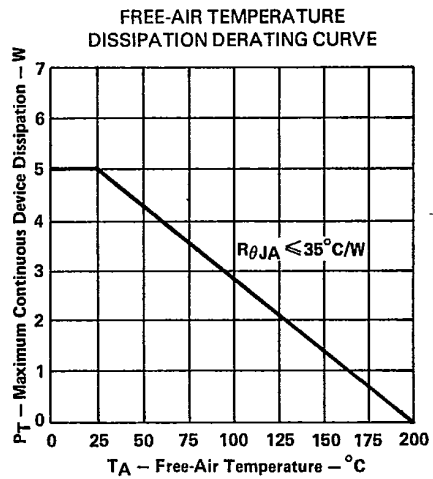


FIGURE 10

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